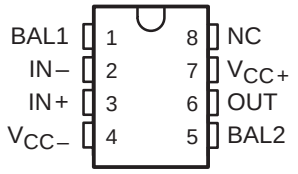
SLOS011C – MARCH 1987 – REVISED OCTOBER 1997

- **Low Input Bias Current, 50 pA Typ**
- **Low Input Noise Current, 0.01 pA/$\sqrt{\text{Hz}}$ Typ**
- **Low Supply Current, 2 mA Typ**
- **High Input impedance, 10^{12} Ω Typ**
- **Low Total Harmonic Distortion**
- **Low 1/f Noise Corner, 50 Hz Typ**
- **Package Options Include Plastic Small-Outline (D) and Standard (P) DIPs**

D OR P PACKAGE
(TOP VIEW)



NC – No internal connection

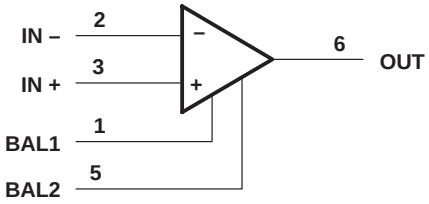
description

This device is a low-cost, high-speed, JFET-input operational amplifier with very low input offset voltage and a maximum input offset voltage drift. It requires low supply current, yet maintains a large gain-bandwidth product and a fast slew rate. In addition, the matched high-voltage JFET input provides very low input bias and offset currents.

The LF411 can be used in applications such as high-speed integrators, digital-to-analog converters, sample-and-hold circuits, and many other circuits.

The LF411C is characterized for operation from 0°C to 70°C. The LF411I is characterized for operation from –40°C to 85°C.

symbol



AVAILABLE OPTIONS

T_A	V_{IO}max AT 25°C	PACKAGE	
		SMALL OUTLINE (D)	PLASTIC DIP (P)
0°C to 70°C	2 mV	LF411CD	LF411CP
–40°C to 85°C	2 mV	LF411ID	LF411IP

The D packages are available taped and reeled. Add the suffix R to the device type (i.e., LF411CDR).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC+} . . . . . 18 V
Supply voltage, V_{CC-} . . . . . –18 V
Differential input voltage, V_{ID} . . . . . ±30 V
Input voltage, V_I (see Note 1) . . . . . ±15 V
Duration of output short circuit . . . . . Unlimited
Continuous total power dissipation . . . . . 500 mW
Package thermal impedance, θ_{JA} (see Note 2): D package . . . . . 197°C/W
P package . . . . . 104°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

NOTES: 1. Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

	C SUFFIX		I SUFFIX		UNIT
	MIN	MAX	MIN	MAX	
Supply voltage, V_{CC+}	3.5	18	3.5	18	V
Supply voltage, V_{CC-}	–3.5	–18	–3.5	–18	V
Operating free-air temperature, T_A	0	70	–40	–85	°C

electrical characteristics over operating free-air temperature range, $V_{CC\pm}$ = ±15 V (unless otherwise specified)

PARAMETER		TEST CONDITIONS		T_A		MIN	TYP	MAX	UNIT
				LF411C	LF411I				
V_{IO}	Input offset voltage	V_{IC} = 0,	R_S = 10 kΩ	25°C	25°C		0.8	2	mV
α_{VIO}	Average temperature coefficient of input offset voltage	V_{IC} = 0,	R_S = 10 kΩ				10	20†	µV/°C
I_{IO}	Input offset current‡	V_{IC} = 0		25°C	25°C		25	100	pA
				70°C	85°C			2	nA
I_{IB}	Input bias current‡	V_{IC} = 0		25°C	25°C		50	200	pA
				70°C	85°C			4	nA
V_{ICR}	Common-mode input voltage range					±11	–11.5 to 14.5		V
V_{OM}	Maximum peak output-voltage swing	R_L = 10 kΩ				±12	±13.5		V
A_{VD}	Large-signal differential voltage	V_O = ±10 V,	R_L = 2 kΩ	25°C	25°C	25	200		V/mV
				0°C to 70°C	–40°C to 85°C	15	200		
r_i	Input resistance	T_J = 25°C					10^{12}		Ω
CMRR	Common-mode rejection ratio	R_S ≤ 10 kΩ				70	100		dB
k_{SVR}	Supply-voltage rejection ratio	See Note 3				70	100		dB
I_{CC}	Supply current						2	3.4	mA

† At least 90% of the devices meet this limit for α_{VIO}.
‡ Input bias currents of an FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperatures as close to the ambient temperature as possible.
NOTE 3: Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

operating characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate		8	13		V/μs
B_1	Unity-gain bandwidth		2.7	3		MHz
V_n	Equivalent input noise voltage	f = 1 kHz, R_S = 20 Ω		18		nV/√Hz
I_n	Equivalent input noise current	f = 1 kHz		0.01		pA/√Hz

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.